



520.36911CX2

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): T. ONO, et al  
Serial No.: 09/249,292  
Filed: February 12, 1999  
For: METHOD AND APPARATUS FOR TREATING SURFACE OF SEMICONDUCTOR  
Group: 1763  
Examiner: A. Olsen

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AMENDMENT

Commissioner for Patents  
Washington, D.C. 20231

December 31, 2002

Sir:

The following amendments and remarks are respectfully submitted in connection with the above-identified application in connection with the accompanying RCE and is responsive to the Advisory Action dated December 24, 2002.

IN THE CLAIMS:

Please amend claim 1 as follows:

1. (thrice amended) A method of treating a surface of a sample, comprising the steps of:
- generating a plasma in a treatment chamber;
  - applying an rf bias voltage of a frequency so that ions of intermediate energy which promote etching reaction while providing poor directionality are reduced, and ions of high energy having a high directionality and ions of low energy which do not contribute to etching are increased, so as to have at least one peak point at a region of high ion energy and at least one peak point at a region of low ion energy for anisotropic etching, and the rf bias voltage to which a peak to peak voltage  $V_{pp}$